

1.0 Table of Contents

1.0	Table of Contents	2
2.0	Purpose.....	4
3.0	Background.....	5
4.0	Experimental Set-up/Procedure	6
5.0	“Test To Failure” Stressing	8
5.1	Device ‘R’ Results and Analysis	8
5.2	Device ‘S’ Results.....	9
5.3	Device ‘T’ Results.....	10
5.4	“Test To Failure” Analysis	11
6.0	Failure Threshold Characterization	11
6.1	Device ‘W’ Results	11
6.2	Device ‘X’ Results	11
7.0	Round Robin Testing.....	12
7.1	Device ‘Y’ Stressing.....	12
7.1.1	<i>Location B Results.....</i>	<i>13</i>
7.1.2	<i>Location C Results.....</i>	<i>13</i>
7.1.3	<i>Location D Results</i>	<i>14</i>
7.1.4	<i>Location E Results.....</i>	<i>15</i>
7.1.5	<i>Device ‘Y’ Analysis.....</i>	<i>15</i>
7.2	Device ‘Z’ Stressing.....	16
7.2.1	<i>Location B Results.....</i>	<i>16</i>
7.2.2	<i>Location C Results.....</i>	<i>17</i>
7.2.3	<i>Location D Results</i>	<i>17</i>
7.2.4	<i>Location E Results.....</i>	<i>18</i>
7.2.5	<i>Device ‘Z’ Analysis.....</i>	<i>18</i>
8.0	Discharge Waveform Comparison.....	19
8.1	Shorting Wire Parameters	20
8.1.1	<i>First Peak Current, I_{P1}</i>	<i>20</i>
8.1.2	<i>Second Peak Current, I_{P2}.....</i>	<i>20</i>
8.1.3	<i>Major Pulse Period, T_{PM}.....</i>	<i>21</i>
8.1.4	<i>5%-40% Risetime, T_{R(5-40)}.....</i>	<i>21</i>
8.1.5	<i>10%-90% Risetime, T_{R(10-90)}.....</i>	<i>22</i>
8.1.6	<i>Waveform Overlay.....</i>	<i>22</i>

8.2	500Ω Load Parameters	23
8.2.1	<i>Peak Current, IPR</i>	23
8.2.2	<i>5%-40% Risetime, TR(5-40)</i>	24
8.2.3	<i>10%-90% Risetime, TR(10-90)</i>	25
9.0	Summary	26
10.0	Conclusion.....	27
11.0	Acknowledgments.....	27
12.0	References	27